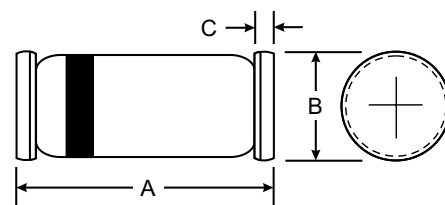


**Features**

- Silicon Epitaxial Planar Diode
- Low Reverse Current and Low Forward Voltage
- Low Current Rectification and High Speed Switching
- High Reliability

**Mechanical Data**



LL34/ SOD-80		
Dim	Min	Max
<b>A</b>	3.30	3.70
<b>B</b>	1.30	1.60
<b>C</b>	0.28	0.50
<b>All Dimensions in mm</b>		

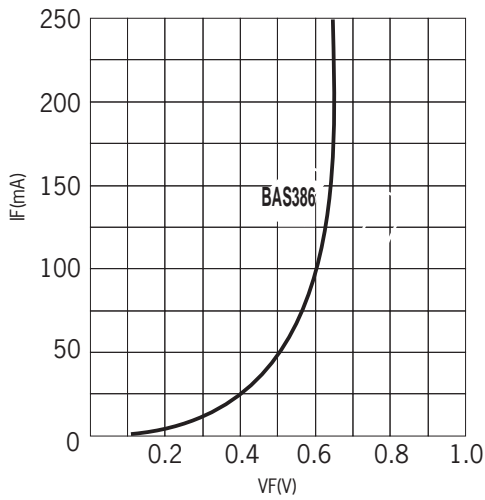
- Case: SOD-80/LL34, Glass
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.05 grams (approx.)

**Maximum Ratings** @ T<sub>A</sub> = 25°C unless otherwise specified

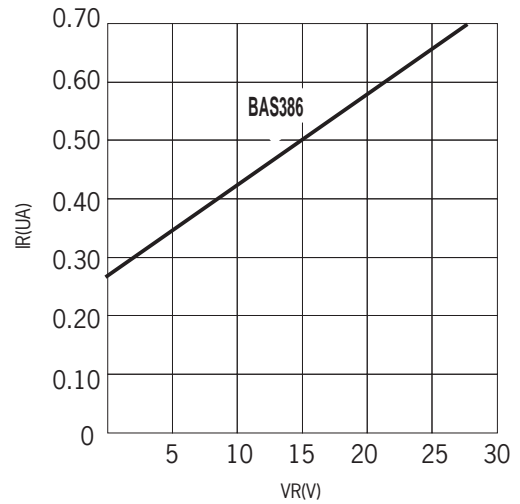
Characteristic	Symbol	BAS386	Unit
Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	45	V
Non-Repetitive Peak Forward Surge Current @t=1S	I <sub>FSM</sub>	500	mA
Forward Continuous Current, T <sub>A</sub> = 25°C	I <sub>F</sub>	50	mA
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +125	°C

**Electrical Characteristics** @ T<sub>A</sub> = 25°C unless otherwise specified

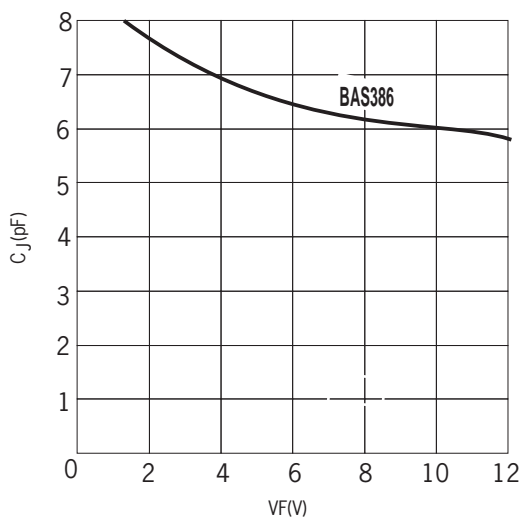
Characteristic	Symbol	Min	Tpy	Max	Unit
Forward Voltage I <sub>F</sub> =1 mA      BAS386 I <sub>F</sub> =200 mA     BAS386	V <sub>F</sub>	-	0.24 0.65	0.5 1.0	V
Reverse Current V <sub>R</sub> =15V      BAS386	I <sub>R</sub>	-	0.5	1.0	uA
Junction Capacitance V <sub>R</sub> =10V, f=1MHz    BAS386	C <sub>j</sub>	-	6.0	-	PF
Reverse Recovery Time I <sub>F</sub> =I <sub>R</sub> =1mA , I <sub>rr</sub> =1 mA, R <sub>c</sub> =100 Ω	T <sub>rr</sub>	-	-	1.0	nS



**FIG.1 Forward Current vs. Forward Voltage**



**FIG.2 Reverse Current vs. Continuous Reverse Voltage**



**FIG.3 Junction Capacitance vs. Continuous Reverse Applied Voltage**